

TOSHIBA IGBT Module Silicon N Channel IGBT

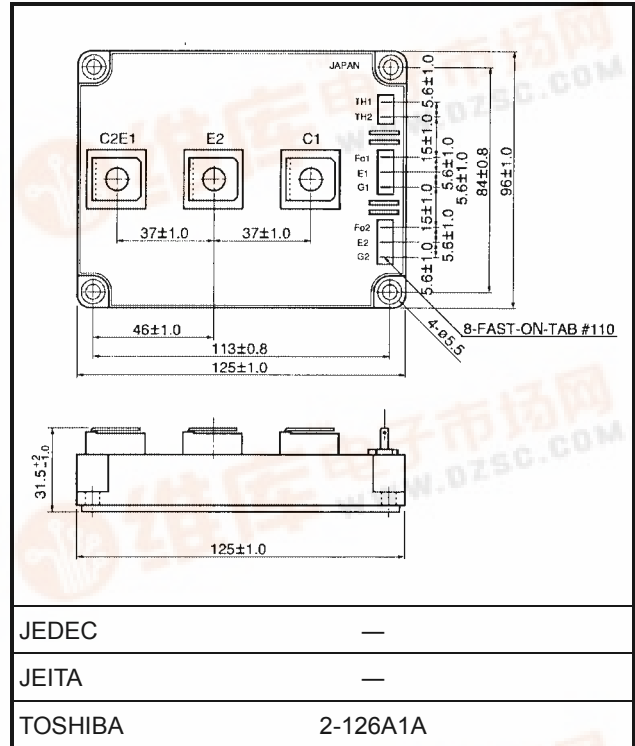
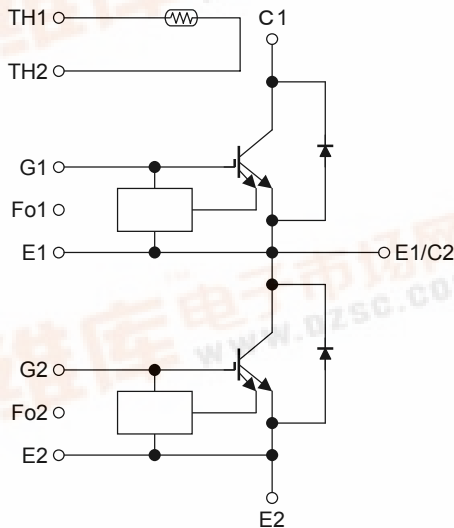
MG800J2YS50A

High power switching applications
Motor control applications

Unit: mm

- The electrodes are isolated from case.
- Enhancement-mode
- Thermal output terminal (TH)

Equivalent Circuit



Weight: 680 g (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-emitter voltage		V_{CES}	600	V
Gate-emitter voltage		V_{GES}	±20	V
Collector current	DC	I_C	800	A
Forward current	DC	I_F	800	A
Collector power dissipation (Tc = 25°C)		P_C	2900	W
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	-40~125	°C
Isolation voltage		V_{isol}	2500 (AC 1 min)	V
Screw torque	Terminal: M8	—	10	N·m
	Mounting: M5	—	3	N·m

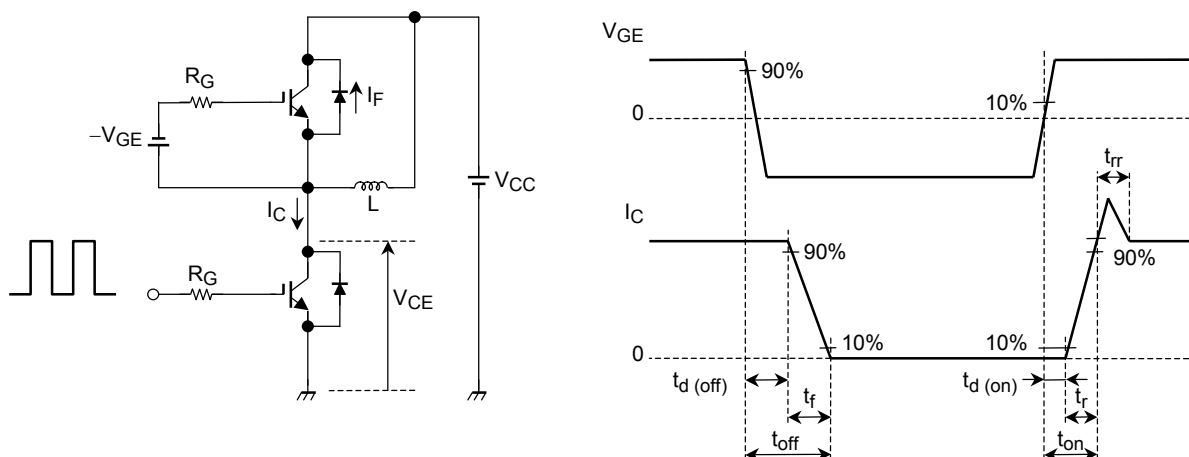
Electrical Characteristics (Ta = 25°C)

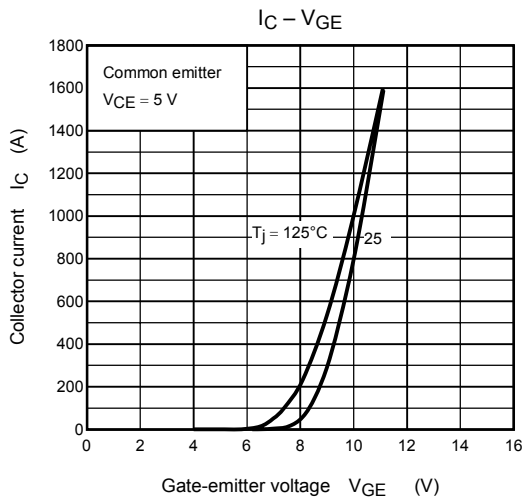
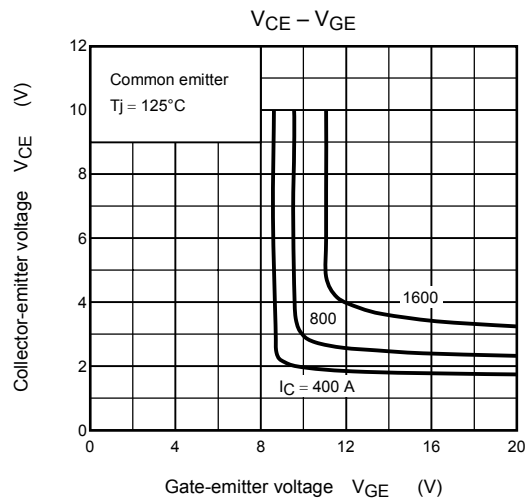
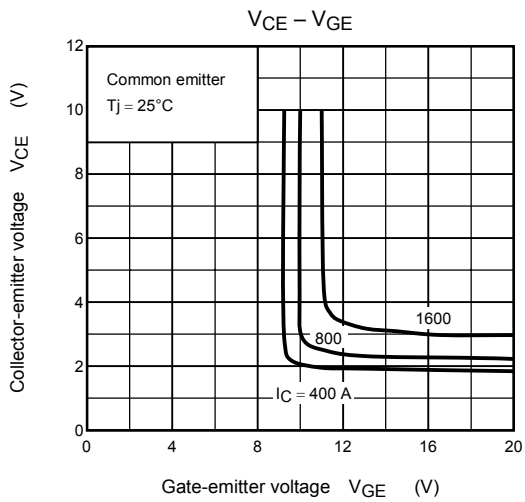
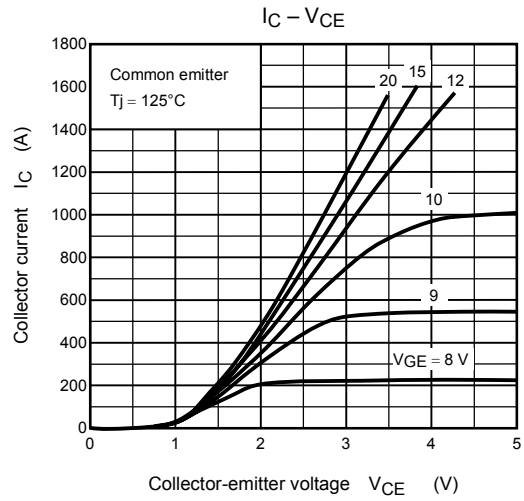
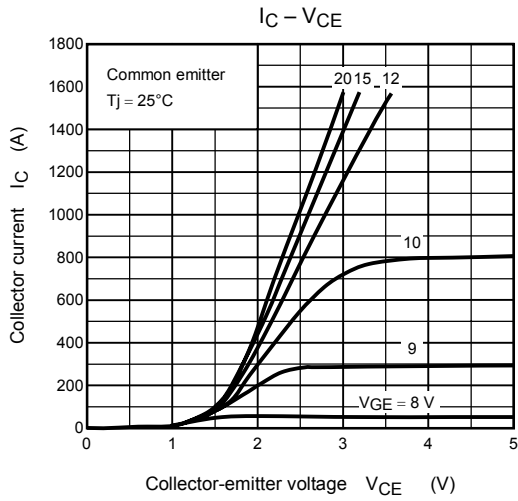
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit	
Gate Leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}, V_{CE} = 0\text{ V}$	—	—	± 10	μA	
Collector cut-off current	I_{CES}	$V_{CE} = 600\text{ V}, V_{GE} = 0\text{ V}$	—	—	1	mA	
Gate-emitter cut-off voltage	$V_{GE (off)}$	$I_C = 800\text{ mA}, V_{CE} = 5\text{ V}$	—	6.5	—	V	
Collector-emitter saturation voltage	$V_{CE (sat)}$	$I_C = 800\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	—	2.4	3.0	V
			$T_j = 125^\circ\text{C}$	—	2.6	3.3	
Input capacitance	C_{ies}	$V_{CE} = 10\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	—	93000	—	pF	
Gate-emitter voltage	V_{GE}	—	13	15	17	V	
Gate resistance	R_G	—	4.7	—	15	Ω	
Switching time	$t_d (on)$	Inductive load $V_{CC} = 300\text{ V}$ $I_C = 800\text{ A}$ $V_{GE} = \pm 15\text{ V}$ $R_G = 4.7\ \Omega$	—	0.3	—	μs	
	t_r		—	0.25	—		
	t_{on}		—	0.55	—		
	$t_d (off)$		—	0.85	—		
	t_f		(Note)	—	0.15		0.30
	t_{off}		—	—	1.05		—
Forward voltage	V_F	$I_F = 800\text{ A}, V_{GE} = 0\text{ V}$	$T_j = 25^\circ\text{C}$	—	2.3	3.0	V
			$T_j = 125^\circ\text{C}$	—	2.1	—	
Reverse recovery time	t_{rr}	$I_F = 800\text{ A}, V_{GE} = -10\text{ V}$ $di/dt = 2000\text{ A}/\mu\text{s}$	—	—	0.5	μs	
Thermal resistance	$R_{th (j-c)}$	Transistor stage	—	—	0.043	C/W	
		Diode stage	—	—	0.056		
RTC Operating current	I_{rtc}	$T_j = 25^\circ\text{C}$	1600	—	—	A	

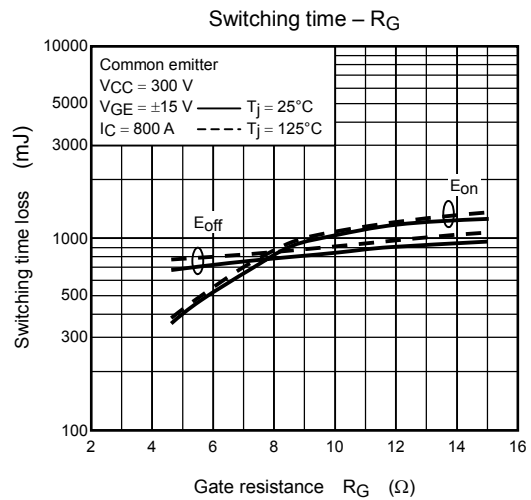
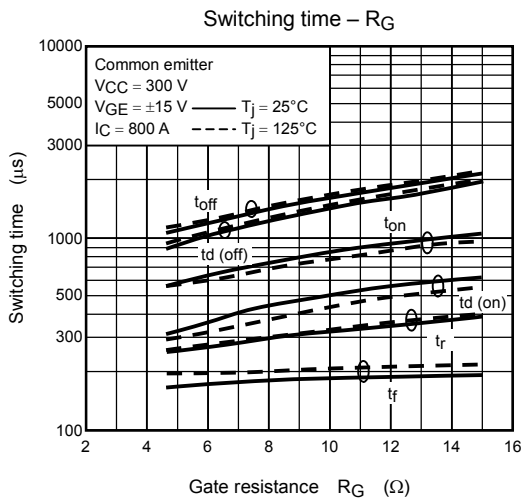
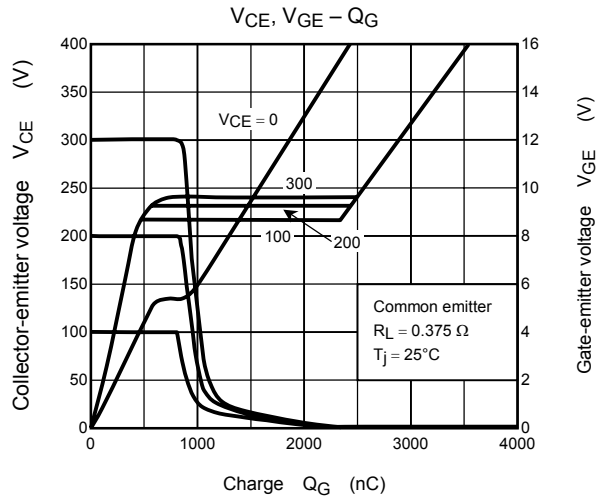
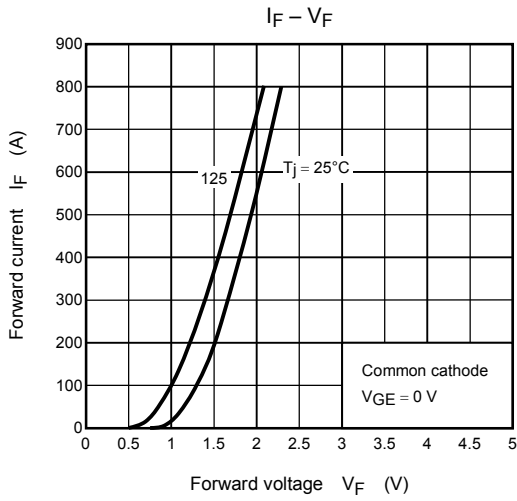
Thermistor

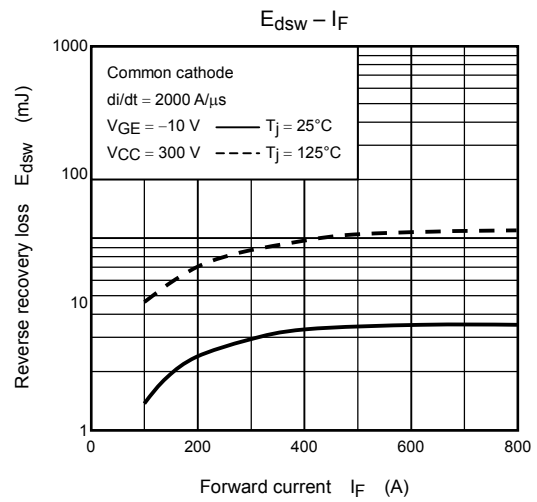
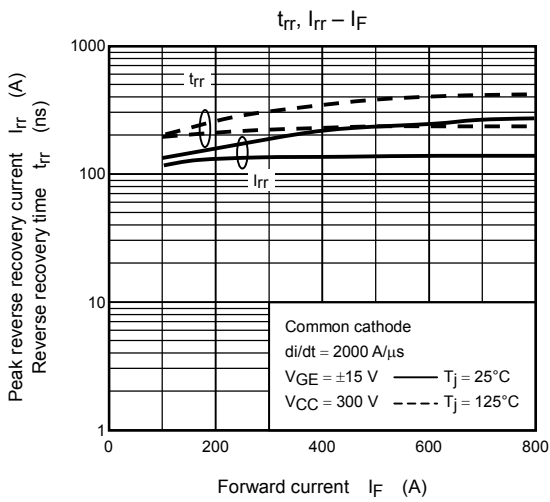
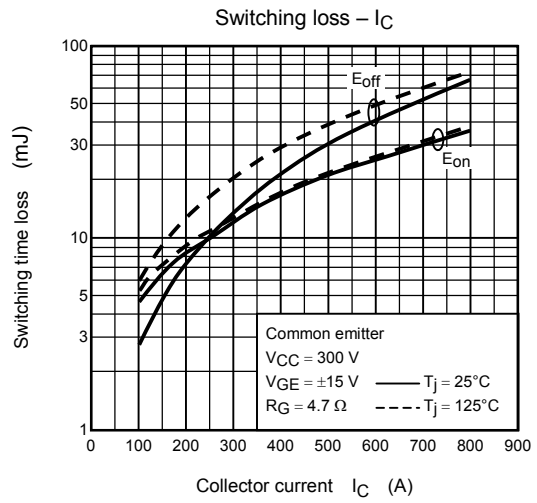
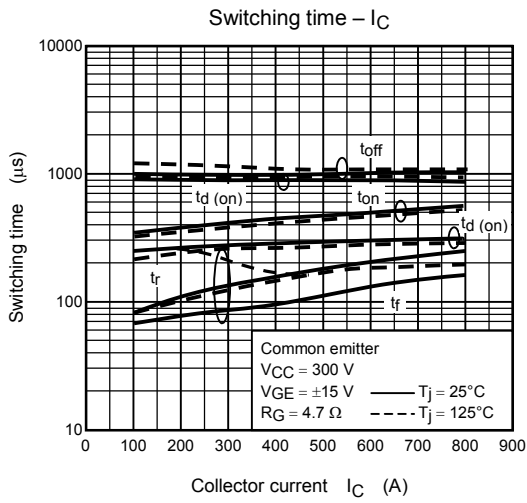
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Zero power resistance	R_{25}	$T_c = 25^\circ\text{C}$	—	100	—	$k\Omega$
B value	$R_{25/85}$	$T_c = 25^\circ\text{C}/T_c = 85^\circ\text{C}$	—	4390	—	K
Isolation voltage		$T_c = 25^\circ\text{C}$	2500	—	—	Vrms

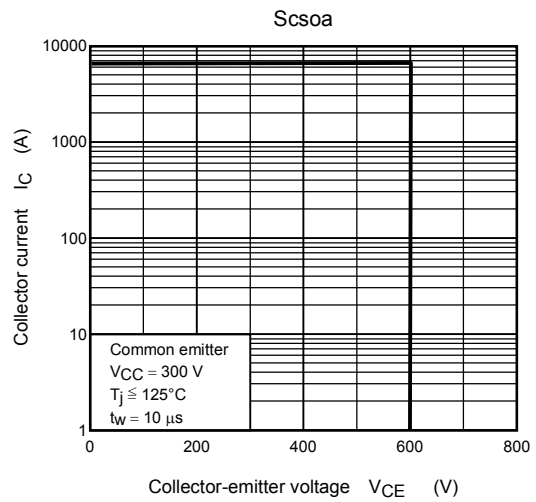
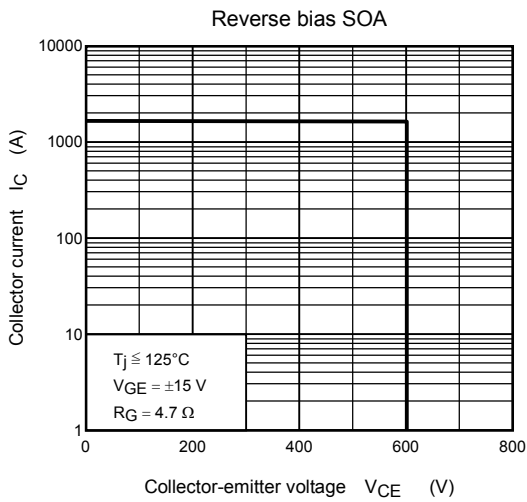
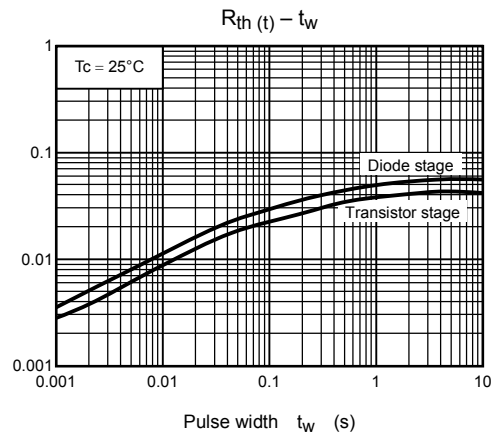
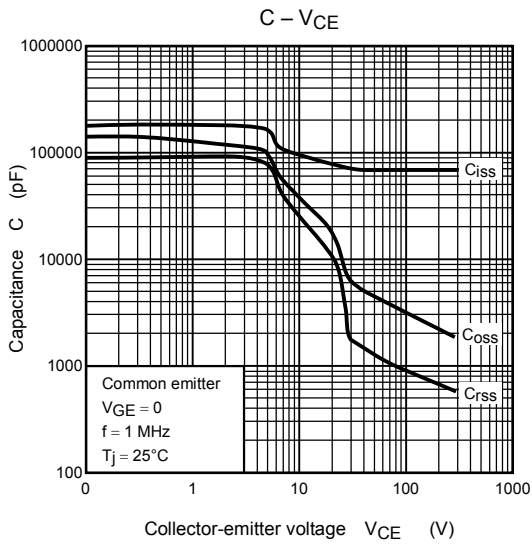
Note: Switching time measurement circuit and input/output waveforms











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